L Number	Hits	Search Text	DB	Time stamp
1	60765	(tft (thin adj film adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:54
2	22061	((tft (thin adj film adj transistor))) and gate and drain and source	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:54
3	18869	(((tft (thin adj film adj transistor))) and gate and drain and source) and substrate.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:55
4	17602	((((tft (thin adj film adj transistor))) and gate and drain and source) and substrate) and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:55
5	15033	(((((tft (thin adj film adj transistor))) and gate and drain and source) and substrate) and electrode) and (method process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:56
6	13007	((((((tft (thin adj film adj transistor))) and gate and drain and source) and substrate) and electrode) and (method process)) and (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:56
7	3555	(((((((tft (thin adj film adj transistor))) and gate and drain and source) and substrate) and electrode) and (method process)) and (gate adj electrode)) and (gate adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:56
8	2141	((((((((tft (thin adj film adj transistor))) and gate and drain and source) and substrate) and electrode) and (method process)) and (gate adj electrode)) and (gate adj line)) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:57
9	958	(((((((((tft (thin adj film adj transistor))) and gate and drain and source) and substrate) and electrode) and (method process)) and (gate adj electrode)) and (gate adj line)) and mask) and reflect$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:57
10	2141	((((((((((tft (thin adj film adj transistor))) and gate and drain and source) and substrate) and electrode) and (method process)) and (gate adj electrode)) and (gate adj line)) and mask) and (reflect$3 (line layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:58
11	80	((((((((((tft (thin adj film adj transistor))) and gate and drain and source) and substrate) and electrode) and (method process)) and (gate adj electrode)) and (gate adj line)) and mask) and (reflect$3 adj (line layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:58
12	15	(((((((((((tft (thin adj film adj transistor))) and gate and drain and source) and substrate) and electrode) and (method process)) and (gate adj electrode)) and (gate adj line)) and mask) and (reflect$3 adj (line layer))) and (ohmic near1 (contact layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:59
13	41	(((((((((((tft (thin adj film adj transistor))) and gate and drain and source) and substrate) and electrode) and (method process)) and (gate adj electrode)) and (gate adj line)) and mask) and (reflect$3 adj (line layer))) and transmissive	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:59

14	12	(((((((((((tft (thin adj film adj transistor))) and gate and drain and source) and substrate) and electrode) and (method process)) and (gate adj electrode)) and (gate adj line)) and mask) and (reflect$3 adj (line layer))) and transmissive) and (ohmic near1 (contact layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:59
15	1	6620655.URPN.	USPAT	2004/05/14 11:01
16	0	6697138.URPN.	USPAT	2004/05/14 11:01
17	3	("6512560" | "6532045" | "6620655" | "2001/0022638" | "2002/0063824" | "2002/0093609").PN.	USPAT	2004/05/14 11:01